# 2SD2242, 2SD2242A

### Silicon NPN triple diffusion planar type Darlington

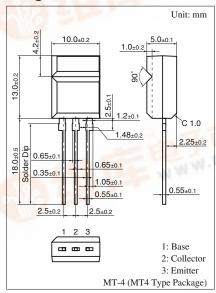
#### For power amplification

#### ■ Features

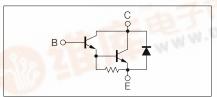
- High forward current transfer ratio h<sub>FE</sub>
- High-speed switching
- Allowing supply with the radial taping

#### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter		Symbol	Rating	Unit
Collector to base	2SD2242	$V_{CBO}$	60	V
voltage	2SD2242A		80	
Collector to	2SD2242	V <sub>CEO</sub>	60	V
emitter voltage	2SD2242A		80	
Emitter to base voltage		V <sub>EBO</sub>	5	V
Peak collector current		$I_{CP}$	8	A
Collector current		$I_{C}$	4	A
Collector power	$T_C = 25^{\circ}C$	$P_{C}$	15	W
dissipation	$T_a = 25^{\circ}C$		2	
Junction temperature		T <sub>j</sub>	150	°C
Storage temperature		$T_{stg}$	-55 to +150	°C



#### **Internal Connection**

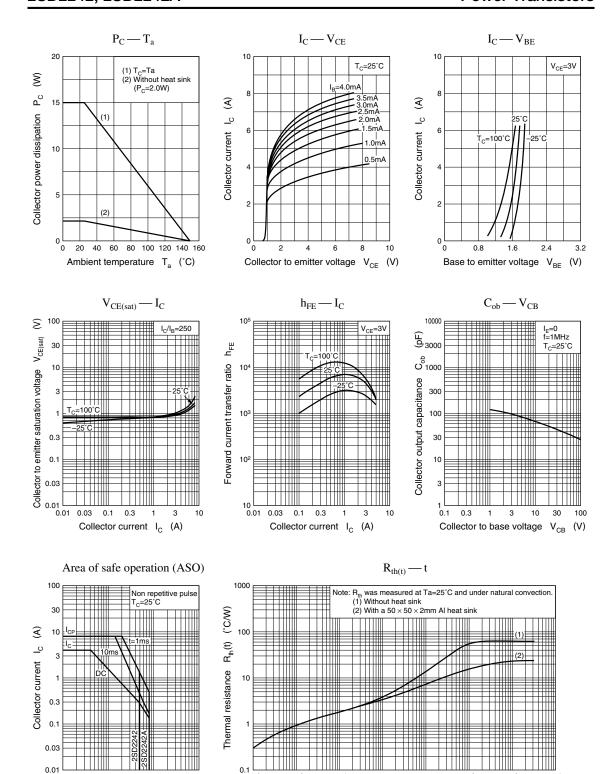


#### ■ Electrical Characteristics $T_C = 25$ °C

Paramete	er	Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff	2SD2242	$I_{CBO}$	$V_{CB} = 60 \text{ V}, I_{E} = 0$			200	μΑ
current	2SD2242A		$V_{CB} = 80 \text{ V}, I_{E} = 0$			200	
Collector cutoff	2SD2242	$I_{CEO}$	$V_{CE} = 30 \text{ V}, I_{B} = 0$			500	μΑ
current	2SD2242A		$V_{CE} = 40 \text{ V}, I_{B} = 0$			500	
Emitter cutoff current		$I_{EBO}$	$V_{EB} = 5 \text{ V}, I_{C} = 0$			2	μΑ
Collector to emitter	2SD2242	V <sub>CEO</sub>	$I_C = 30 \text{ mA}, I_B = 0$	60	His	- 4	V
voltage	2SD2242A		190	80			
Forward current transfer ratio		h <sub>FE1</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 0.5 \text{ A}$	1 000			
		h <sub>FE2</sub> *	$V_{CE} = 3 \text{ V}, I_{C} = 3 \text{ A}$	2 000		10 000	
Base to emitter voltag	e	$V_{\mathrm{BE}}$	$V_{CE} = 3 \text{ V}, I_{C} = 3 \text{ A}$			2.5	V
Collector to emitter saturation voltage		V <sub>CE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 12 \text{ mA}$			2	V
			$I_C = 5 \text{ A}, I_B = 20 \text{ mA}$			4	
Transition frequency		$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time		t <sub>on</sub>	$I_C = 3 \text{ A}, I_{B1} = 12 \text{ mA}, I_{B2} = -12 \text{ mA},$		0.5		μs
Storage time		t <sub>stg</sub>	$V_{CC} = 50 \text{ V}$		4		μs
Fall time		t <sub>f</sub>			1		μs

Note Rank classification

Rank	Q	R		
h <sub>FE2</sub>	2 000 to 5 000	4 000 to 10 000		



10-2

10-1

Time t (s)

30 100

Collector to emitter voltage  $V_{CE}$  (V)

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